## slide 6:

To figure out the component over Vbe, we need to find out the relationship between ib and Vbe in this circuit branch.

## slide 7:

we know that:

$$i_{g} = \frac{i_{e}}{\beta} = \frac{J_{s}}{\beta} \exp^{(\frac{V_{g}}{b_{f}})}$$

therefore, the component over Use is a PN diode.

## 5/12/13:

When a small perturbation is added in the input side:

= Ico + gm Vm sinwt

= 1 co + gmVin

$$I_{c} = I_{s} \exp \left(\frac{(V_{o} + V_{in})V_{T}}{V_{T}}\right) = I_{s} \exp \left(\frac{V_{m}sinwt}{V_{T}}\right)$$

$$= I_{co} \cdot \exp \left(\frac{V_{m}sinwt}{V_{T}}\right)$$

$$\approx I_{co} \cdot \left(1 + \frac{V_{m}sinwt}{V_{T}}\right)$$

$$= I_{co} + \lim_{N \to \infty} \frac{I_{co}}{V_{T}} V_{m}sinwt$$

$$e^{\chi} \approx 1 + \chi \quad \text{when } \chi = c$$

according to Ic = Ico + gavin,

the circuit is therefore divided into two parts.

## Slide 15:

In Small-signal model:

$$i_B = \frac{g_m V_{in}}{B}$$

$$R = \frac{v_{in}}{i_B} = \frac{\beta}{g_m}$$

therefore: a resister with a value of  $\frac{8}{3}m$  is determined, which is different from the large-signal model that is modeled with a pN Junction.